

**1. Scope :**

This specification applies to InGaAs PIN photodiode chips.  
Device No. ED-MPD25VB

**2. Structure :**

- 2-1. Type : PIN diode.  
2-2. Electrodes :  
Top side ( Anode ) : Au alloy.  
Back side ( Cathode ) : Au alloy.

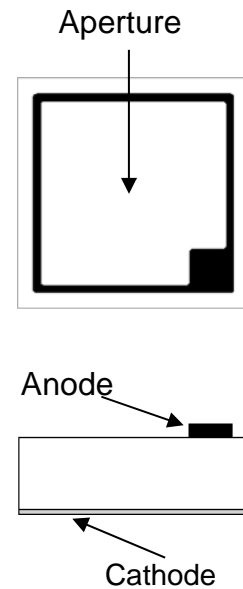
**3. Size :**

- 3-1. Chip size : 24.7 mils × 24.7 mils (0.628 mm × 0.628 mm).  
3-2. Chip thickness : 7.9 ± 1 mils (0.20 ± 0.025 mm).  
3-3. Aperture size : 19.7 mils × 19.7 mils (0.50 mm x 0.50 mm).  
3-4. Bonding pad ( Anode ) : 3.9 x 3.9 mils (0.100 mm x 0.100mm).  
3-5. Pattern drawing : Refer to the attached drawing.

**4. Electro-optical characteristics (Ta = 25 °C)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
* Reverse Dark Current	$I_D$	$V_R=5V$ $E_e=0mW/cm^2$	-	-	1	nA
* Reverse Breakdown Voltage	$V_R$	$I_R=1\mu A$ $E_e=0mW/cm^2$	30	-	-	V
* Forward Voltage	$V_F$	$I_F=3mA$ $E_e=0mW/cm^2$	-	-	0.7	V
Capacitance	$C_p$	$V_R=5V$ $f=1MHz$	-	-	20	pF
Responsivity	Resp	$V_R=5V$ Wavelength =1310nm	0.8	-	-	A/W

\*Based on 100% probing



5. Typical Electro-Optical Characteristics Curve:

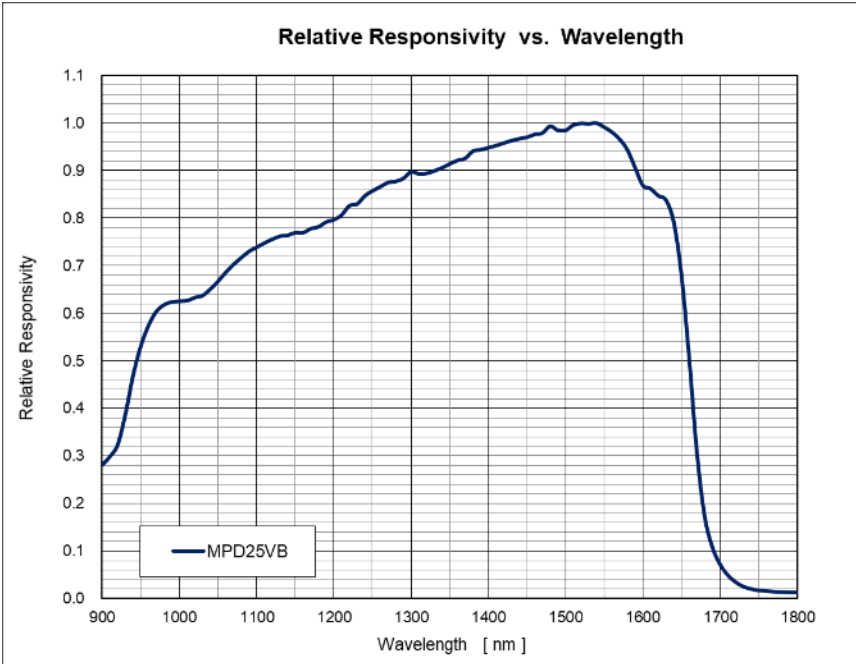


Fig 1. Relative Responsivity vs Wavelength

